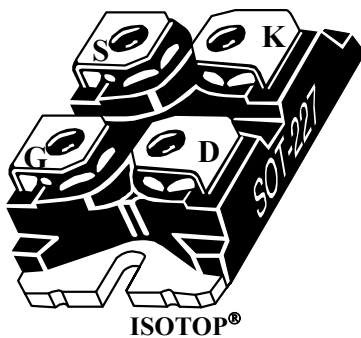
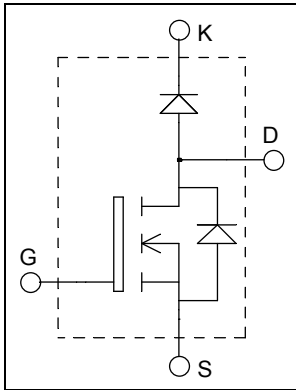


**ISOTOP<sup>®</sup> Boost chopper  
 MOSFET + SiC chopper diode  
 Power module**

**$V_{DSS} = 1000V$**   
 **$R_{DSon} = 330m\Omega$  typ @  $T_j = 25^\circ C$**   
 **$I_D = 26A$  @  $T_c = 25^\circ C$**


**Application**

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

**Features**

- **Power MOS 8<sup>TM</sup> MOSFET**
  - Low  $R_{DSon}$
  - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
- **SiC Schottky Diode**
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature Independent switching behavior
  - Positive temperature coefficient on VF
- ISOTOP<sup>®</sup> Package (SOT-227)
- Very low stray inductance
- High level of integration

**Benefits**

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- RoHS Compliant

**Absolute maximum ratings**

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	1000	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	26
		$T_c = 80^\circ C$	20
$I_{DM}$	Pulsed Drain current	140	A
$V_{GS}$	Gate - Source Voltage	$\pm 30$	V
$R_{DSon}$	Drain - Source ON Resistance	396	m $\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	543
$I_{AR}$	Avalanche current (repetitive and non repetitive)	18	A

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 1000\text{V}$ $V_{GS} = 0\text{V}$	$T_j = 25^\circ\text{C}$		100	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$		500	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 18\text{A}$		330	396	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5\text{mA}$	3	4	5	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}$			$\pm 100$	$\text{nA}$

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}$		7868		$\text{pF}$
$C_{oss}$	Output Capacitance	$V_{DS} = 25\text{V}$		825		
$C_{rss}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$		104		
$Q_g$	Total gate Charge	$V_{GS} = 10\text{V}$ $V_{Bus} = 500\text{V}$ $I_D = 18\text{A}$		305		$\text{nC}$
$Q_{gs}$	Gate – Source Charge			55		
$Q_{gd}$	Gate – Drain Charge			145		
$T_{d(on)}$	Turn-on Delay Time	<b>Resistive switching @ <math>25^\circ\text{C}</math></b> $V_{GS} = 15\text{V}$ $V_{Bus} = 667\text{V}$ $I_D = 18\text{A}$ $R_G = 2.2\Omega$		44		$\text{ns}$
$T_r$	Rise Time			40		
$T_{d(off)}$	Turn-off Delay Time			150		
$T_f$	Fall Time			38		

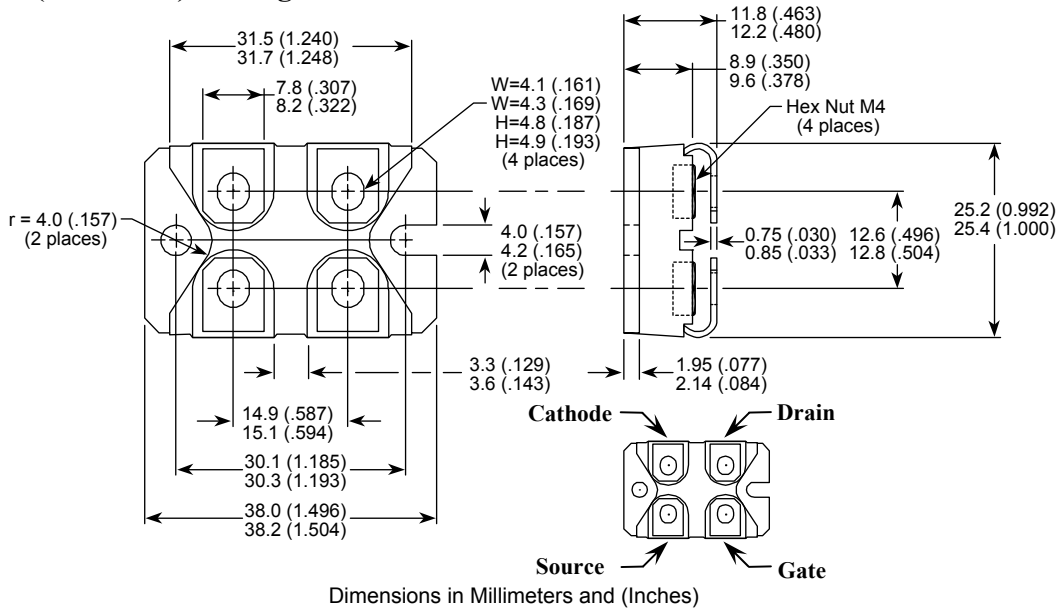
**SiC chopper diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		1200			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$	$T_j = 25^\circ\text{C}$	32	200	$\mu\text{A}$
			$T_j = 175^\circ\text{C}$	56	1000	
$I_F$	DC Forward Current	$T_c = 100^\circ\text{C}$		10		A
$V_F$	Diode Forward Voltage	$I_F = 10\text{A}$	$T_j = 25^\circ\text{C}$	1.6	1.8	V
			$T_j = 175^\circ\text{C}$	2.3	3	
$Q_C$	Total Capacitive Charge	$I_F = 10\text{A}, V_R = 600\text{V}$ $di/dt = 500\text{A}/\mu\text{s}$		80		$\text{nC}$
C	Total Capacitance	$f = 1\text{MHz}, V_R = 200\text{V}$		96		$\text{pF}$
		$f = 1\text{MHz}, V_R = 400\text{V}$		69		

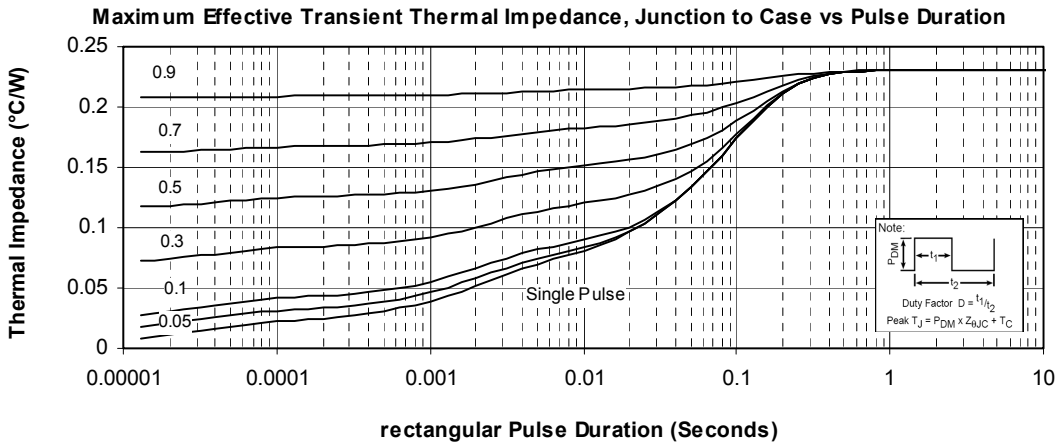
**Thermal and package characteristics**

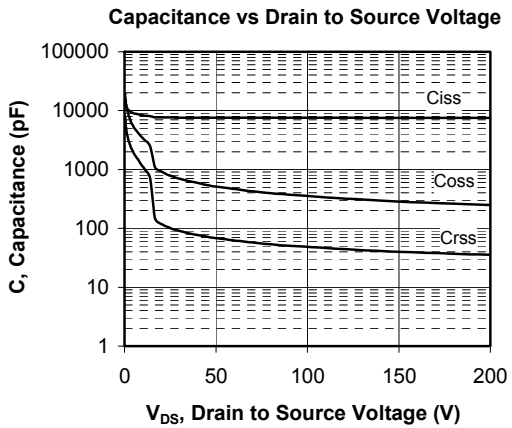
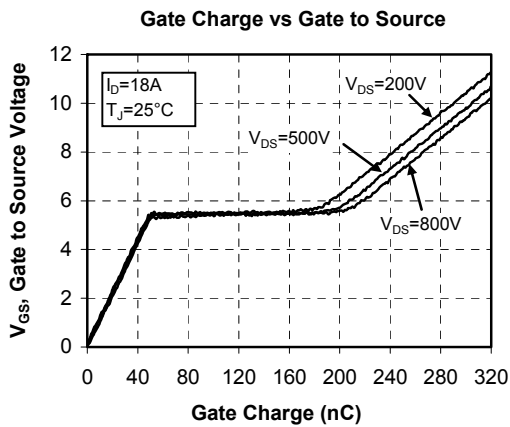
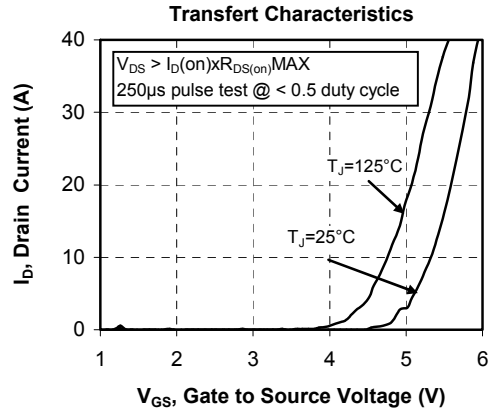
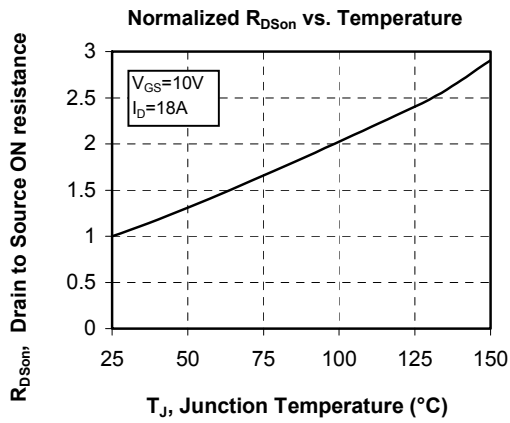
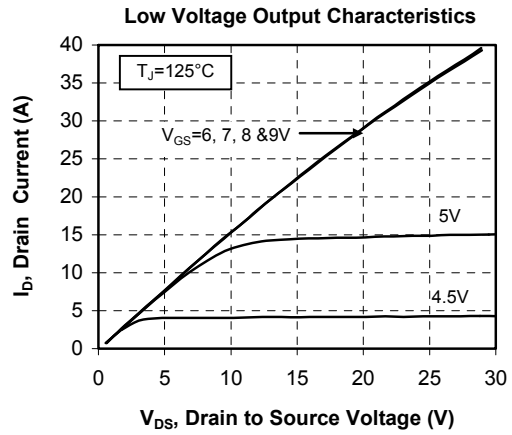
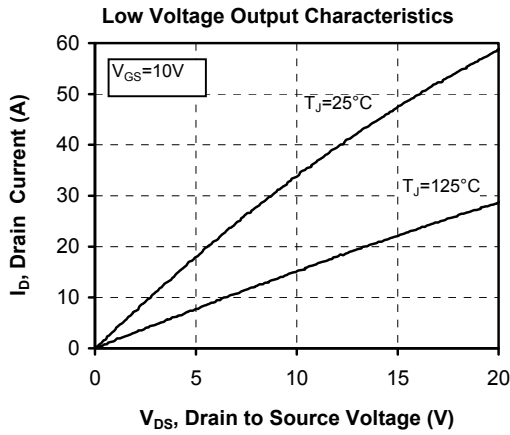
Symbol	Characteristic	Min	Typ	Max	Unit
$R_{thJC}$	Junction to Case Thermal Resistance	Mosfet		0.23	$^\circ\text{C}/\text{W}$
		SiC Diode		1.65	
$R_{thJA}$	Junction to Ambient (IGBT & Diode)			20	$^\circ\text{C}/\text{W}$
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case $t = 1\text{min}, 50/60\text{Hz}$	2500			V
$T_J, T_{STG}$	Storage Temperature Range	-40		150	$^\circ\text{C}$
$T_L$	Max Lead Temp for Soldering: 0.063" from case for 10 sec			300	$^\circ\text{C}$
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)			1.5	N.m
Wt	Package Weight		29.2		g

**SOT-227 (ISOTOP®) Package Outline**

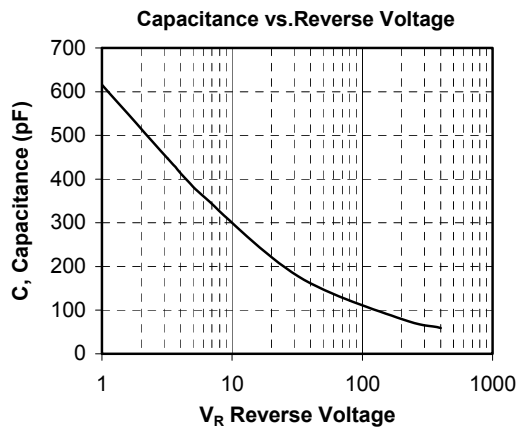
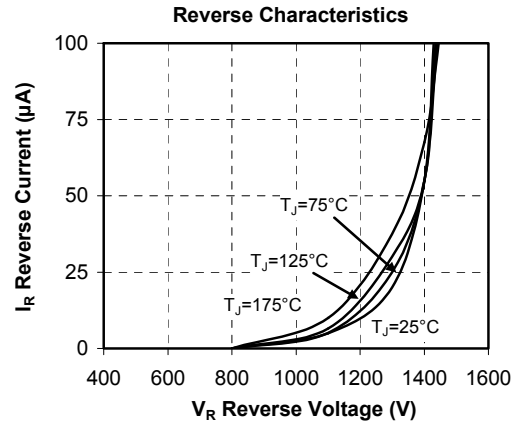
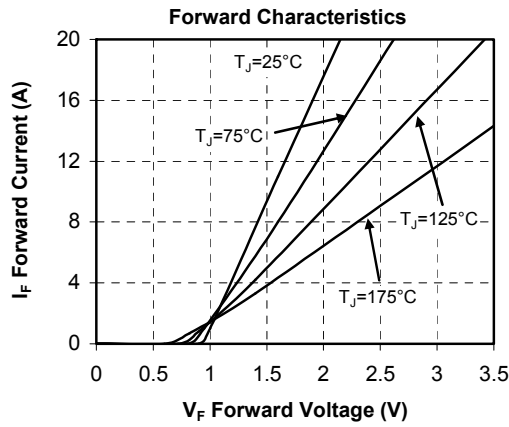
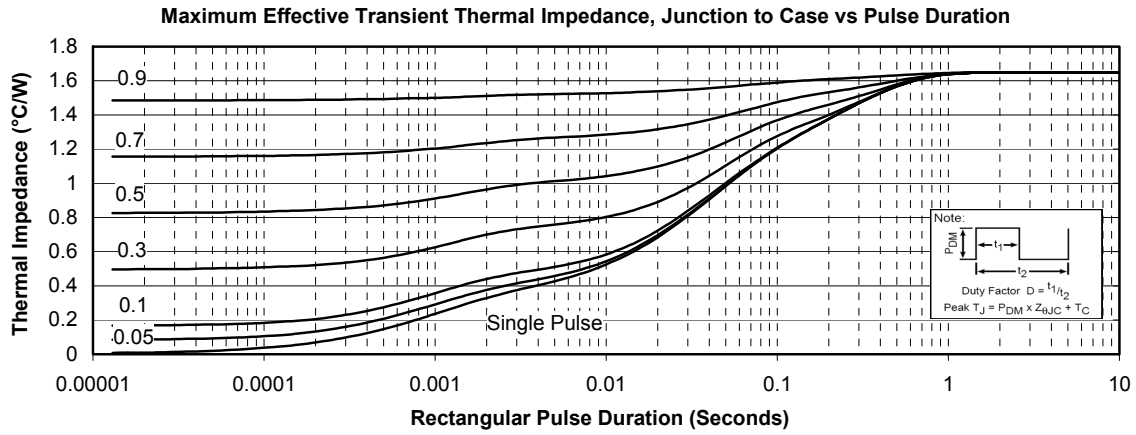


**Typical Mosfet Performance Curve**





## Typical SiC Diode Performance Curve



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